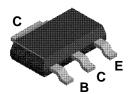


July 1998

NZT660 / NZT660A



SOT-223

PNP Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous.

Absolute Maximum Ratings* T_{A=2}

T_{A = 25°C unless otherwise noted}

Symbol	Parameter	NZT660/NZT660A	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	3	А
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

 $^{{}^{\}star}\text{These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.}$

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

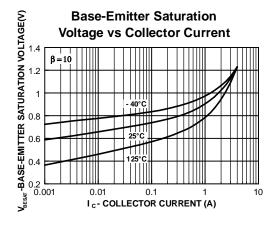
Thermal Characteristics T_{A = 25°C unless otherwise noted}

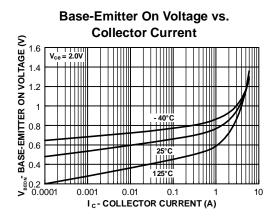
Symbol	Characteristic	Max	Units
		NZT660/NZT660A	
P _D	Total Device Dissipation	2	W
R _θ JA	Thermal Resistance, Junction to Ambient	62.5	°C/W

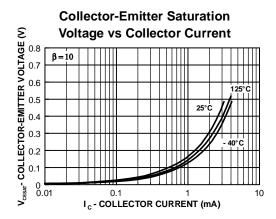
Symbol	Parameter	Min	Max	Units	
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA	60		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA	80		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA	5		V
Ісво	Collector Cutoff Current	V _{CB} = 30 V V _{CB} = 30 V, T _A =100°C		100 10	nA uA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V		100	nA
ON CHAR	ACTERISTICS*				
h _{FE}	DC Current Gain	$I_C = 100 \text{ mA}, V_{CE} = 2 \text{ V}$	70		-
		I _C = 500 mA, V _{CE} = 2 V NZT660 NZT660A	100 250	300 550	
		$I_C = 1 A$, $V_{CE} = 2 V$	80		
		I _C = 3 A, V _{CE} = 2 V	25		
	0 11 1			300	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 1 A$, $I_B = 100 \text{ mA}$		000	mV
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 3 \text{ A}, I_B = 300 \text{ mA}$ NZT660		550	mV
V _{CE} (sat)	•			550 500	
V _{CE(sat)}	Base-Emitter Saturation Voltage	$I_C = 3 \text{ A}, I_B = 300 \text{ mA}$ NZT660		550	V
V _{BE} (sat)	•	I _C = 3 A, I _B = 300 mA NZT660 NZT660A		550 500	
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 3 A, I _B = 300 mA NZT660 NZT660A I _C = 1 A, I _B = 100 mA		550 500 1.25	V
V _{BE(sat)}	Base-Emitter Saturation Voltage Base-Emitter On Voltage	I _C = 3 A, I _B = 300 mA NZT660 NZT660A I _C = 1 A, I _B = 100 mA		550 500 1.25	V

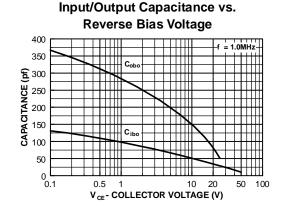
*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

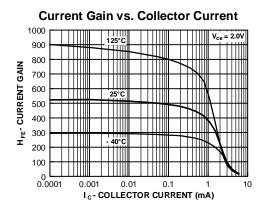
Typical Characteristics







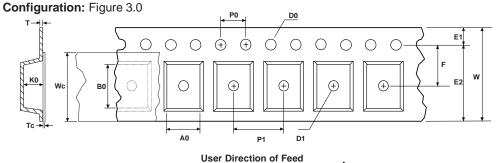








SOT-223 Embossed Carrier Tape

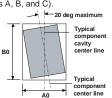


Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

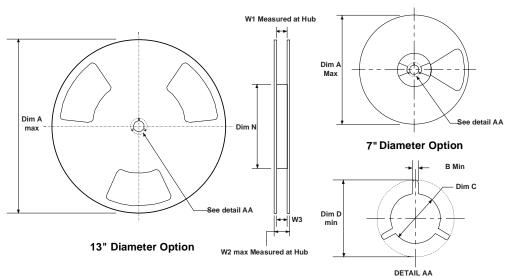


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

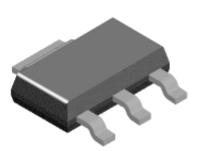
SOT-223 Reel Configuration: Figure 4.0

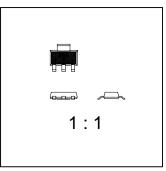


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

SOT-223 Tape and Reel Data and Package Dimensions, continued

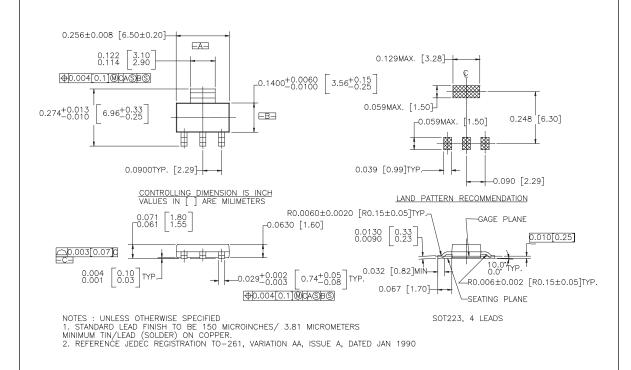
SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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